
InGaAs PIN PHOTODIODES

PD-1100 SERIES

FEATURES

- 2 High responsivity for dual windows at 1310 nm and 1550 nm
- 2 Low dark current
- 2 Quick pulse response
- 2 Hermetically sealed 3-pin metal case
- 2 Active diameter 75 μm

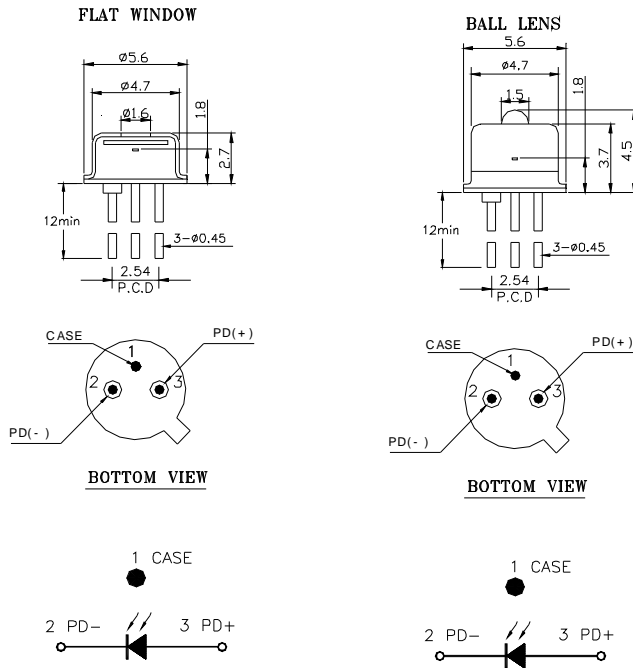
DESCRIPTION

PD-1100 series InGaAs Photodiode are suited to receive the light at the wavelength range from 1100 nm to 1600 nm. With high reliability, PD-1100 series are the best choice for telecom and datacom application.

ELECTRICAL AND OPTICAL CHARACTERISTICS (T _c =25°C)						
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
	Active Area			75		μm
	Detection Range		1100		1600	nm
R	Responsivity	V _R =5V, λ =1300nm	0.85		-	A/W
		V _R =5V, λ =1550nm	0.90			
I _{dark}	Dark Current	V _R =5V		0.3	0.7	nA
C	Capacitance	V _R =5V		0.7	1.0	pF
T _r /T _f	Rise/Fall Time	V _R =5V, 10~90%			0.3	ns
BW	Bandwidth	V _R =5V	2			GHz

ABSOLUTE MAXIMUM RATINGS (T _c =25 °C)			
Symbol	Parameter	Ratings	Unit
P _o	Input Optical Power	10	mW
V _{RD}	Reverse Voltage	20	V
I _{FD}	Forward Current	10	mA
T _{opr}	Operating Temperature	-40~+85	°C
T _{stg}	Storage Temperature	-40~+85	°C

MECHANICAL DIMENSION (mm) and PIN ASSIGNMENT



- Note:**
1. Specifications subject to change without notice.
 2. Other PIN assignment is available upon request.

ORDER INFORMATION

Part No.: P D - 1 1 0 □ - □

Code	Wavelength
1	1310 / 1550 nm
3	1310 nm
5	1550 nm

Code	Package
0	Ball Lens Cap
5	Flat Window Cap

Code	Diameter
Blank	75 μm
100	100 μm
150	150 μm
